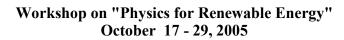


The Abdus Salam International Centre for Theoretical Physics



International Atomic Energy Agency



301/1679-25

"Current Status of Photovoltaics"

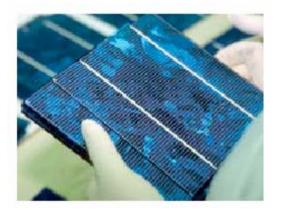
F. Ferrazza EniTechnologie Nettuno (Rome) Italy

Strada Costiera 11, 34014 Trieste, Italy - Tel. +39 040 2240 111; Fax +39 040 224 163 - sci_info@ictp.it, www.ictp.it

Current status of photovoltaics

Francesca Ferrazza EniTecnologie, Nettuno

Workshop on Physics for Renewable Energy

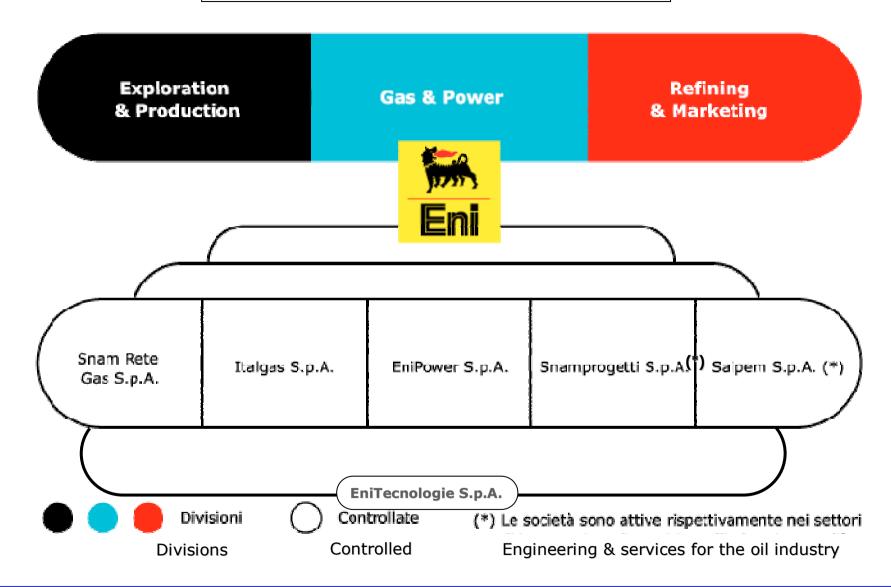


ICTP - Trieste 25 october 2005





Eni Organization







EniTecnologie is the "Corporate Technology Company" of Eni

EniTecnologie operates in the sectors of <u>energy</u>, <u>hydrocarbon</u> <u>derived products and alternative sources</u>, innovating while fully respecting the environment and with a view to sustainability.

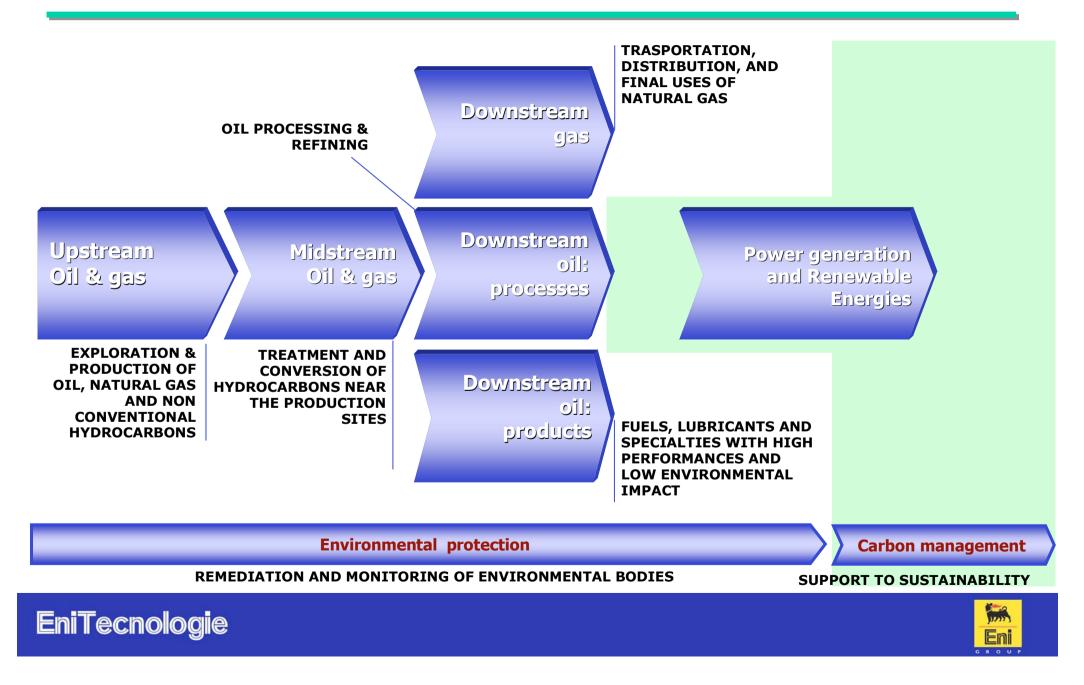
EniTecnologie researches frontier technological ideas in sectors linked to the <u>oil and gas, power generation, renewable energies,</u> <u>fuels and derived products value chains.</u>

EniTecnologie safeguards technological know-how and industrial property in strategic energy sectors and maintains an observatory on the <u>future of technologies and on technological</u> <u>innovation strategies</u> at an international level.





SECTORS OF INTEREST FOR ENI



EniTecnologie, the Corporate Technology Company of Eni, is one of the major centres of excellence for the industrial research. It works in the oil and gas whole technology chain and in renewable sources, while safeguarding the environment, in a sustainable development perspective.

EniTecnologie took over Eurosolare, the Eni company that develops, produces and markets photovoltaic modules.





Inner Mongolia, 2004 Rural electrification Italy, petrol station Grid connected





EniTecnologie research centres

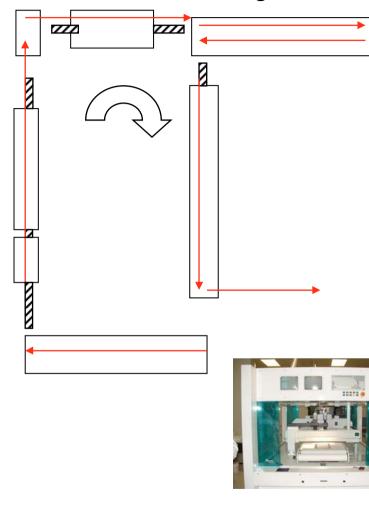


More information available on www.enitecnologie.it



The solar cell production line at EniTecnologie, Nettuno







- in line spray-on doper
- in line ceramic roller furnace
- SiN ARC
- screen printed metallization
- automation in progress

Full capacity 12 MW/yr



AAAAAA



Contents

- Market
- Technology
- Future developments
- Conclusions

"Photovoltaics literally means light-electricity: photo comes from the Greek *phos*, meaning light, and volt from the Italian scientist *Alessandro Volta*; a pioneer in the study of electricity. This technology, originally developed for space applications in the 1950s, has many advantages: it is modular, clean, easy to maintain, and can be installed almost anywhere to suit the needs of the user. The electricity produced can be used directly, stored locally or fed into an existing electricity grid."

Source: A Vision for PV 2030 and beyond, PV TRAC report 2005

http://europa.eu.int/comm/research/rtdinfo/index _en.html





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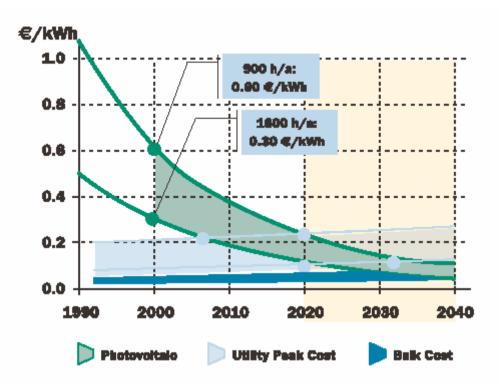




Table 3: Electricity production from renewable sources, technical potential of RES and electricity generation costs

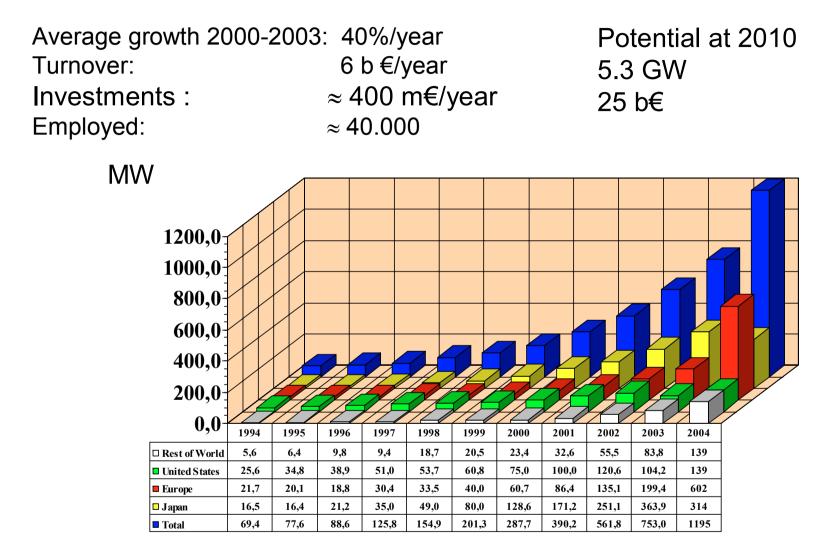
	World electricity production 2003 (TWh)	World energy technical potential heat and electricity (x 1 000 TWh/year ^{ae})	Electricity generation costs 2003 (€cents/kWh)
Hydroelectricity	2 631	14	2 - 8
Blo-energy	175	>77	5-6
Wind energy	75	178	4 - 12
Geothermal power	50	1400	2 - 10
Marine energy	0.8	32	[8 - 15]*
Solar thermal energy	0.5	. 115	12 - 18
PV	2,5	>440	25 - 65
Total renewable electricity production	2 969	>2 100	
Total world consumption To	Electricity ~ 16,700 tal primary energy ~ 120,0	00	
* estimated costs			

World Energy Assessment: Energy and the challenge of Sustainability, UNDP, New York, ISBN 92-1-1261-0 (Chapter 5: Energy Resources)





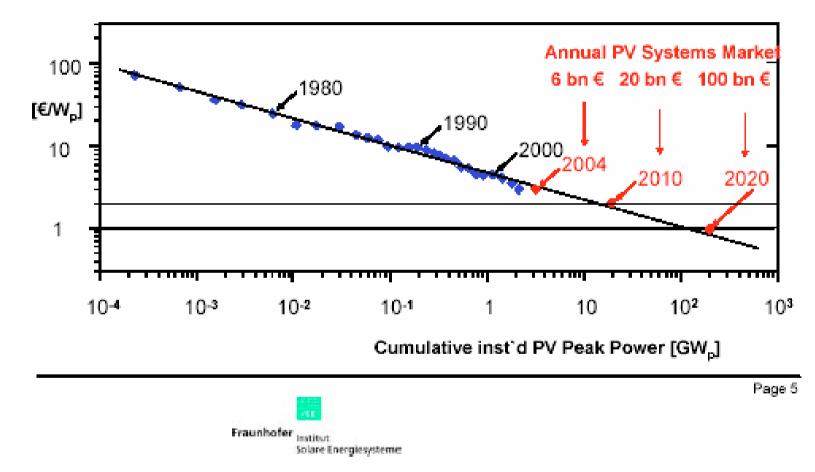
World Market



Fonte: IEA, PPSP, SolarBuzz, PV News, PV Status report JRC 2005



Price Experience Curve of Crystalline Si PV Modules





Incentives for PV in Europe (grid connected)

Country	Feed in tariff	capital incentives	loans	tax incentives	Notes
Austria					Installations 2003-04
Belgio					15c€/KWh
Cipro					12 - 26 c€/KWh
Rep. Ceca					20 c€/KWh
Danimarca					Green tariff under discussion
Estonia				•	
Finlanda					
Francia	•				15c€/KWh
Germania	•				55 c€/KWh
Grecia	•		•		7,8 c€/KWh
Irlanda					Under discussion
Italia	•				45 - 49 c€/KWh
Lituania	•				56 c€/KWh
Lussemburgo	•	•			25 - 45 c€/KWh
Malta					
Paesi Bassi	•				6,8 c€/KWh
Polonia			•		
Portogallo	•				22,4- 41 c€/KWh
Regno Unito			•		
Slovacchia					
Slovenia	•				6,5-37 c€/KWh
Spagna					21.6-39.6 c€/KWh
Svezia					
Svizzera					10 c€/KWh
Ungheria					60 c€/KWh

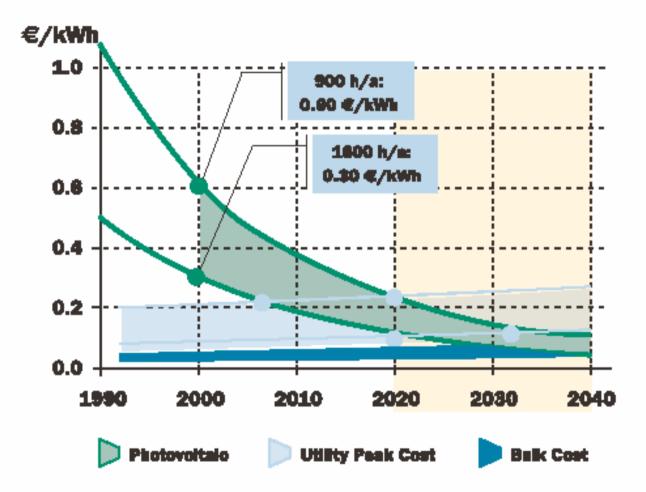


Market players

	2004	Production	Share	Ave growth	Capacity 2006/7
		(MW)		1999-2004	(estimates)
1	Sharp	314	26,3%	80%	800
2	Kyocera	105	8,8%	37%	480
3	BP Solar	85	7,1%	30%	202
4	Shell Solar	72	6,0%	35%	149
5	Mitsubishi	73	6,1%	64%	230
6	Rwe Schott Solar	64	5,4%	59%	202
7	Sanyo	64	5,4%	52%	398
8	Isofoton	54	4,5%	81%	202
9	Q-cells	73	6,1%	69%	499
10	Motech	35	2,9%	37%	230
11	General Electric	25	2,1%	(**)	70
12	Suntech	28	2,3%	(***)	202
	Total top ten	992	83,0%		
	others	203	17,0%		1138
	Total sales	1195	100,0%		4800





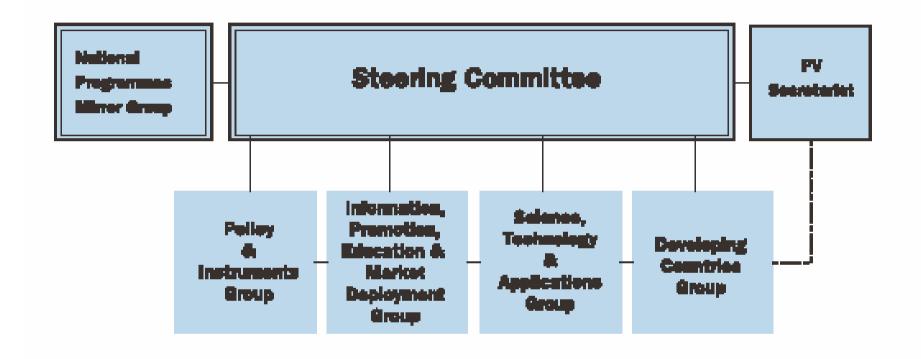


28 EPIA: Towards an Effective Industrial Policy for PV (RWE Schott Solar)





Figure 6: PV Technology Platform structure as proposed by PV-TRAC





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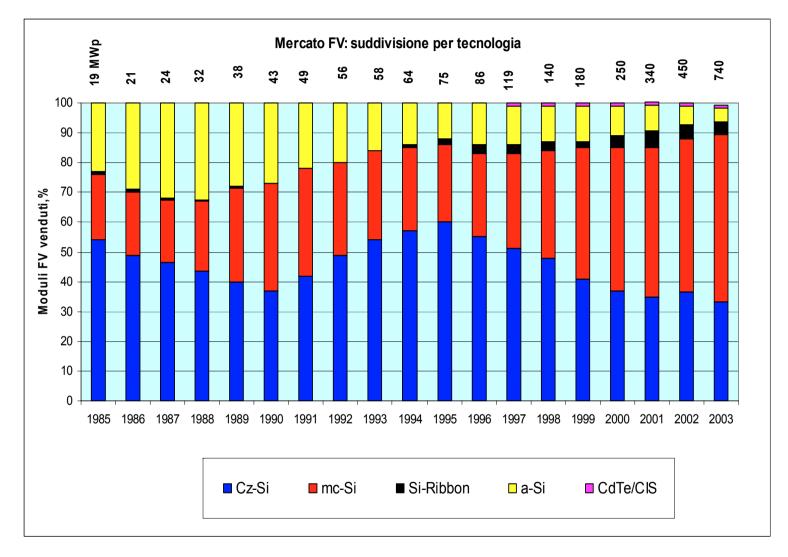


Bell Labs, 1955



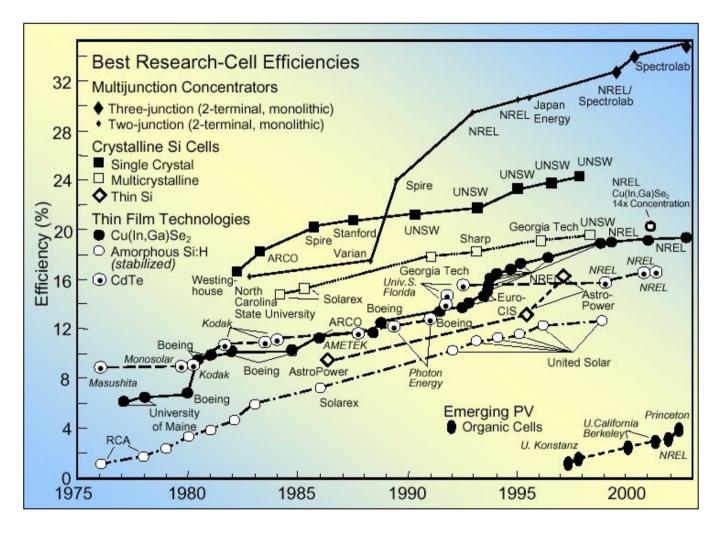


Market by technology





Cell record chart

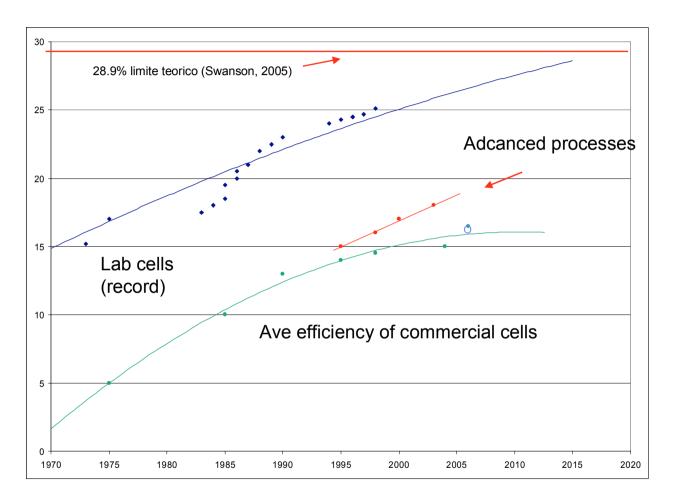


Source – NREL, US





The case of silicon: Lab records and commercial cells

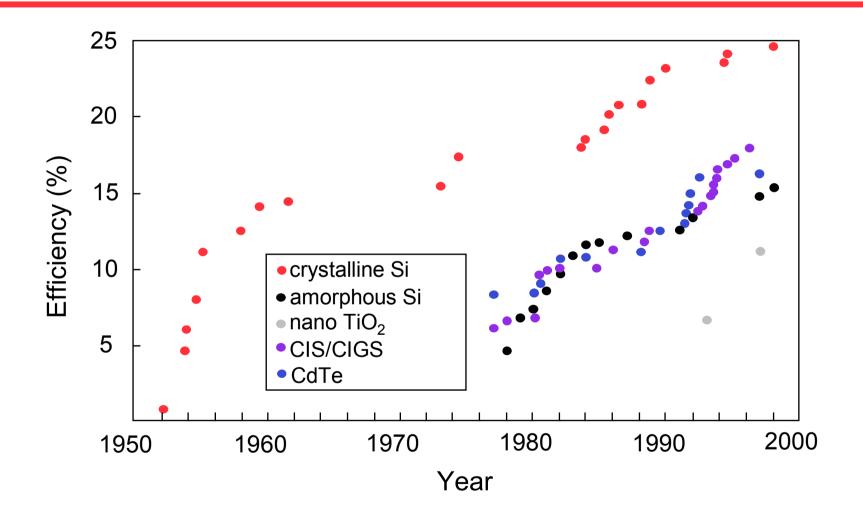


Fonte: Progress in Photovoltaics,UNSW web site, Conf records ET 2005



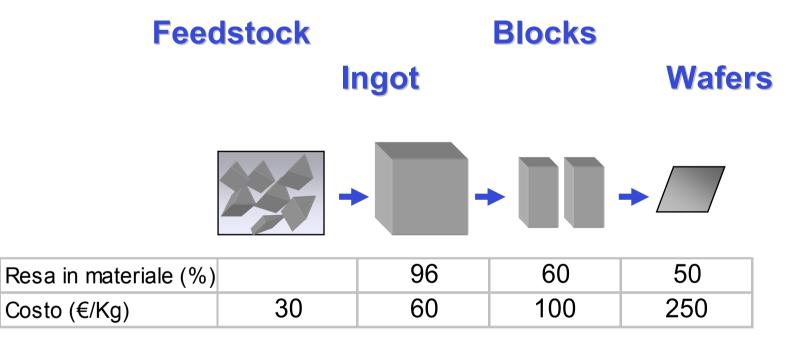


Efficiency of Photovoltaic Devices





Silicio - material yield

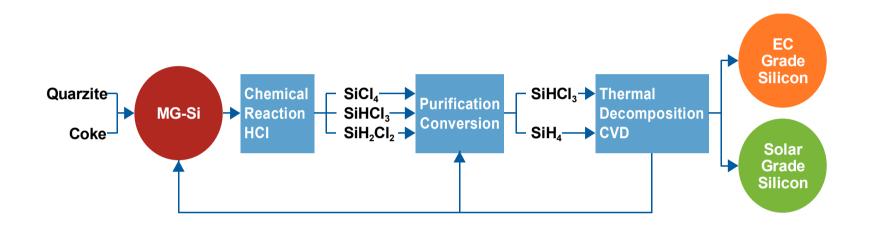


1 wafer = (3 ± ,3) € (125 mm² 270 μm)





Il silicio per uso fotovoltaico - I

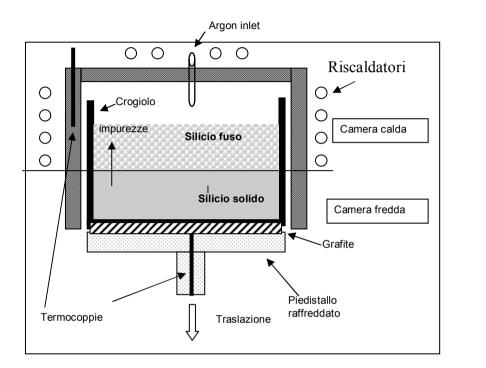


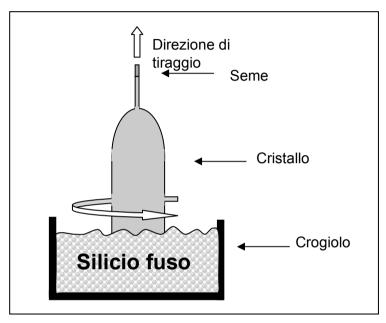
Shortage in feedstock supply





Silicon for PV – ingot growth





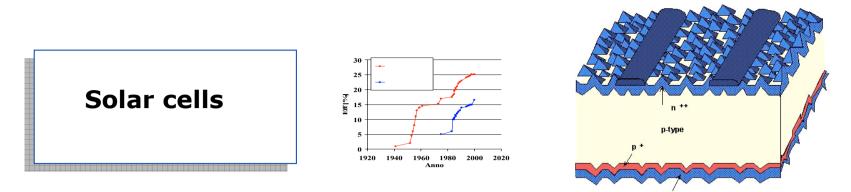
Schematic of Directional Solidification For mutlicrystalline silicon



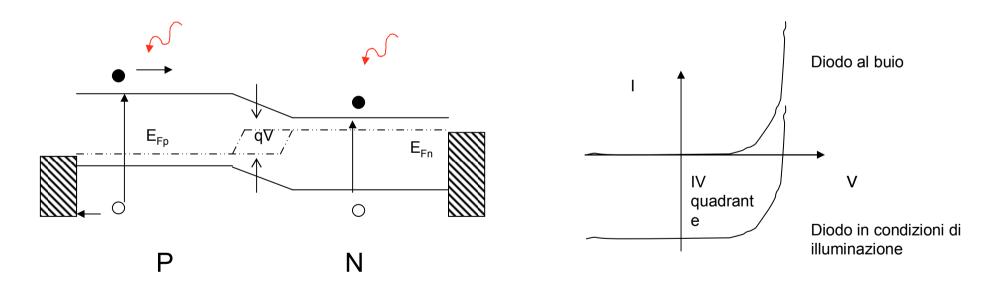
Schematic of Czochralski growth







Commercial solar cells ar p-n diodes on thin silicon substrates. The metal contacts are realized by screen printing metal pastes.







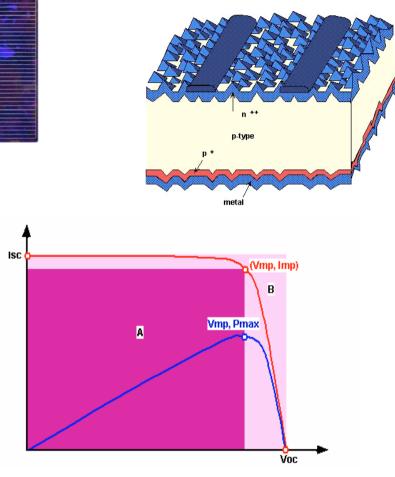


Efficiency 14 -15% on multicrystalline silicon 15 –16% on CZ Si

Eff=Pcell/P standard Sun Standard Sun = 1000W/m² spectrum AM1.5G

Typical wafer dimensions 100 cm², 150 cm²,

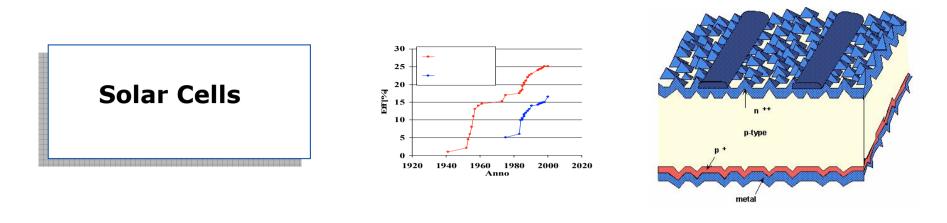
Thickness <270 μ m

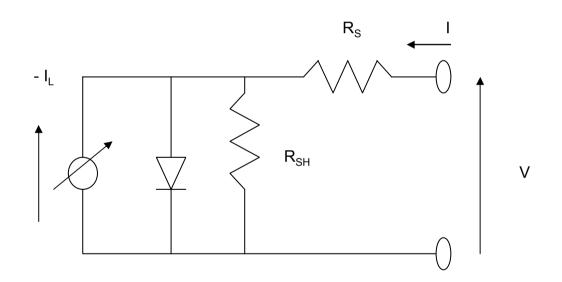


 $FF = I_{mp}V_{mp}/I_{sc}V_{oc}$









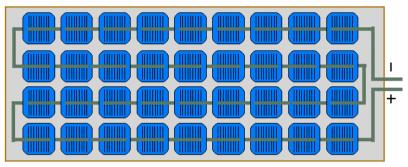
Simplified circuit schematic of a pn solar cell

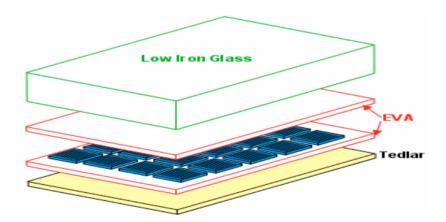




Schematic of a PV module

A typic al module has 36 cells in series





Lifetime >20 years Type certification (IEC 61215)





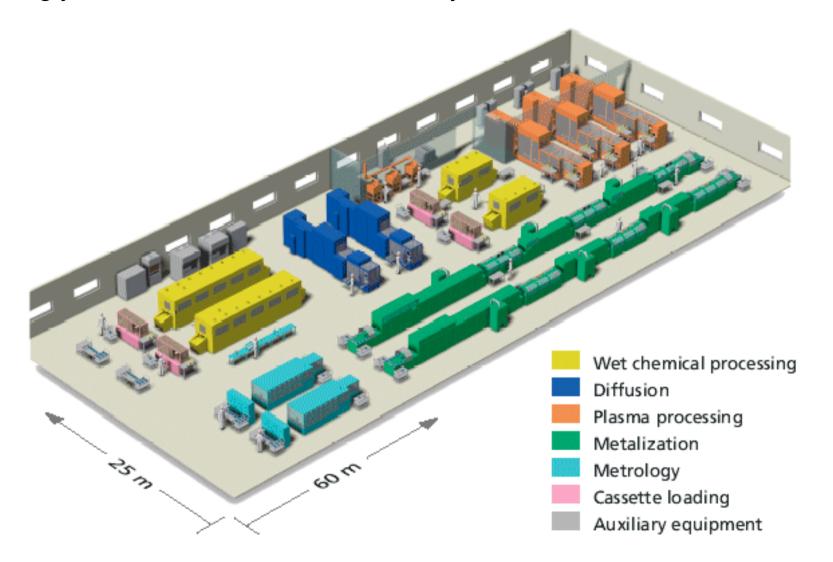
Semi-automatic line 5 MW/year - 1990







Strongly automated batch line – 40 MW/year - 2001







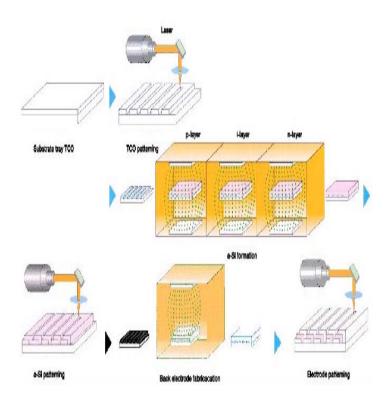
50MW/year, 2003

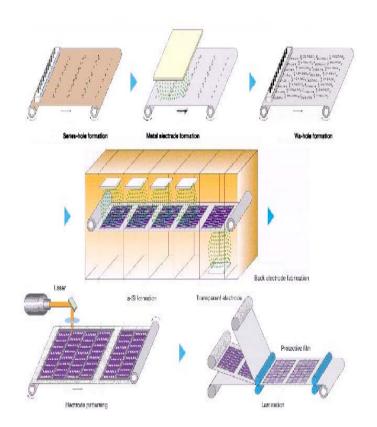






Thin films



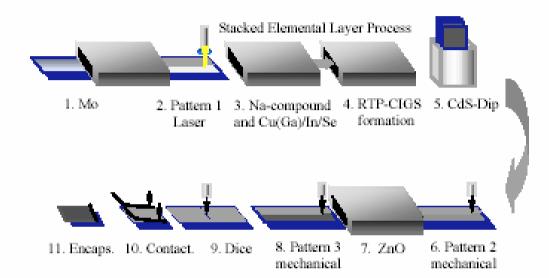




Thin films – what's the situation?

Open problems

- Low efficiency (<10%)
- Stability
- Toxic or rare materials
- Complex technologies
- Expensive equipment



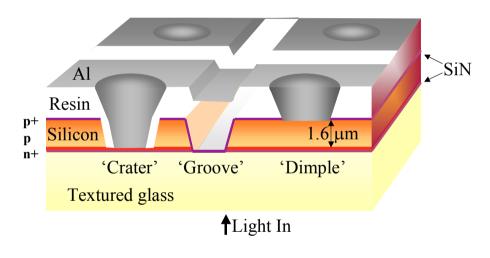
Advantages

- Low material usage => potential low cost
- Cell and module in the same sequence
- High industrial potential
- Aesthetical aspect



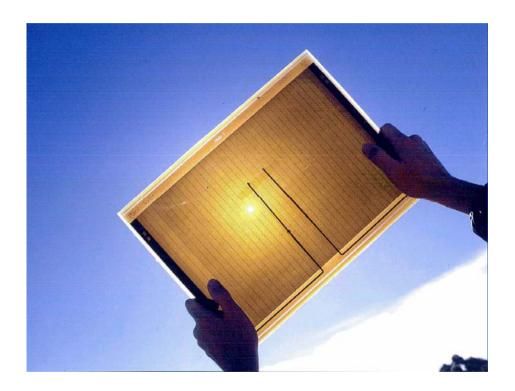
Thin Polycrystalline silicon on glass:

Ave eff 7.5% (Pacific Solar, now CSG Solar)



Schema di una sezione

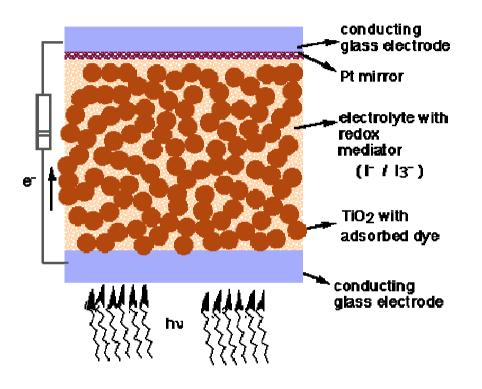
Other thin films: a-Si, CdTe, CIS





Nanotecnologies:

Dye sensitized Nanocrystalline Solar Cell (DYSC)

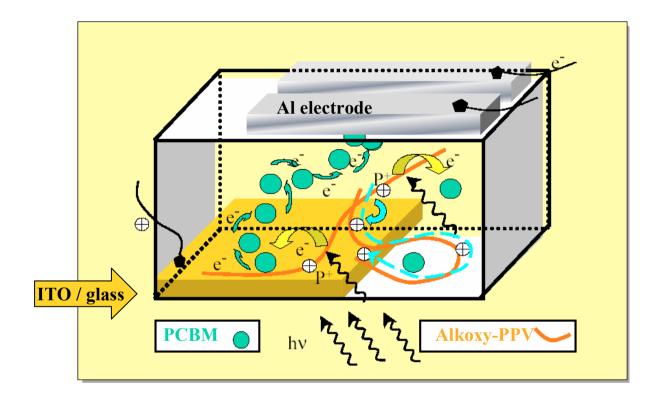


Efficiency up to 10% on small area





Polimeric cell – University of Linz



Schema di funzionamento della Cella polimerica MDMO = PPV 3,7-dimethyloctyloxy methyloxy PPV PCBM = 1-(3-methoxycarbonyl) propyl-1-phenyl [6,6] **C**₆₁





Polimer solar cells - Dresden

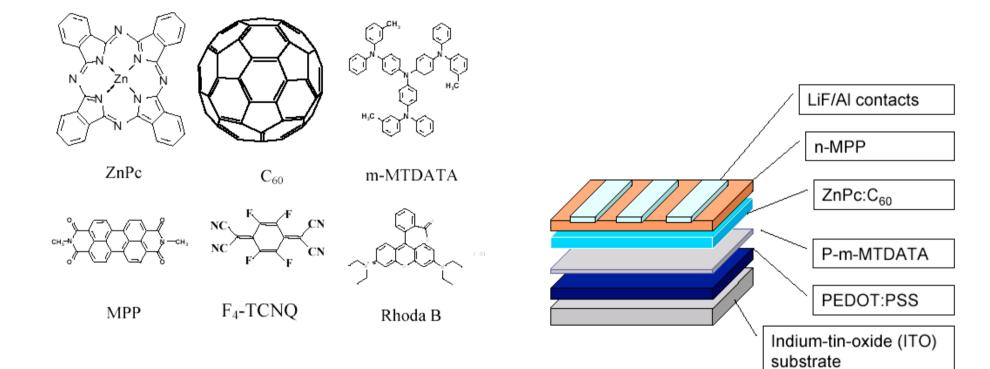


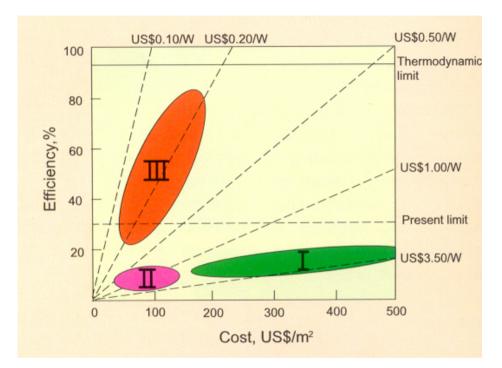
Fig. 1: Schematic diagram of the device configuration and molecular structures of the materials used.





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Medium-long term developments

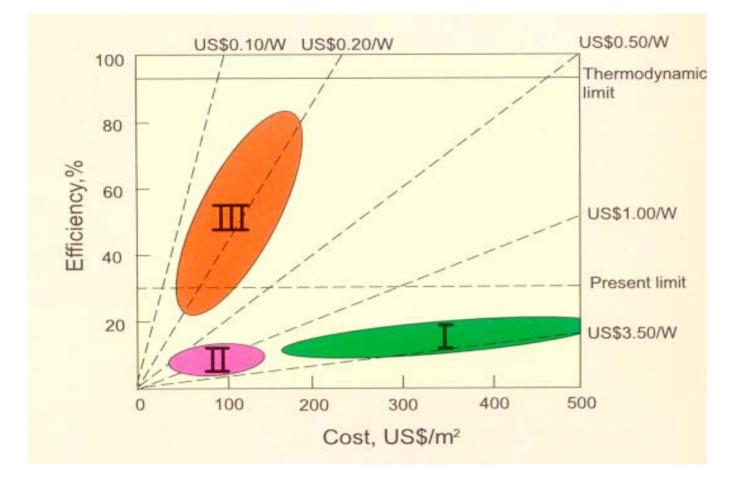
- High efficiency cells on thin (< 250 μ m) large areas (>200 cm²)
- Possible industrial relevance of > 20% efficient processes
- thin films
- nanotecnologies
- very high efficiency cells







High efficiency or low cost?





EniTecnologie

Record chart (1 sun)

Classification ^a	Effic. ^b (%)	Area ^c (cm ²)	V_{∞} (V)	J _∞ (mA/cm ²)	FF ^d (%)	Test centre ^e (and date)	Description
Silicon							
Si (crystalline)	24.7 ± 0.5	4.00 (da)	0.706	42.2	82.8	Sandia (3/99)	UNSW PERL ⁶
Si (multicrystalline)	19.8 ± 0.5	1.09 (ap)	0.654	38-1	79.5	Sandia (2/98)	UNSW/Eurosolare6
Si (thin film transfer)	16.6 ± 0.4	4.017 (ap)	0.645	32.8	78.2	FhG-ISE (7/01)	U. Stuttgart (45 µm thick)7
III-V cells							
GaAs (crystalline)	25.1 ± 0.8	3-91 (t)	1.022	28.2	87.1	NREL (3/90)	Kopin, AlGaAs window
GaAs (thin film)	23.3 ± 0.7	4.00 (ap)	1.011	27.6	83-8	NREL (4/90)	Kopin, 5 µm CLEFT8
GaAs (multicrystalline)	18.2 ± 0.5	4.011 (t)	0.994	23.0	79.7	NREL (11/95)	RTI, Ge substrate9
InP (crystalline)	21.9 ± 0.7	4·02(t)	0.878	29.3	85.4	NREL (4/90)	Spire, epitaxial10
Polycrystalline thin film							
CIGS (cell)	18.4 ± 0.5^{f}	1.04 (ap)	0.669	35.7	77.0	NREL (2/01)	NREL, CIGS on glass ¹¹
CIGS (submodule)	16.6 ± 0.4	16-0 (ap)	2.643	8.35	75-1	FhG-ISE (3/00)	U. Uppsala, 4 serial cells12
CdTe (cell)	16.5 ± 0.5^{f}	1.032 (ap)	0.845	25.9	75.5	NREL (9/01)	NREL, mesa on glass ¹³
Amorphous/Nanocrystalline Si							
Si (nanocrystalline)	10.1 ± 0.2	1-199 (ap)	0.539	24.4	76-6	JOA (12/97)	Kaneka (2 µm on glass) ¹⁴
Photochemical							
Nanocrystalline dye	8.2 ± 0.3	2-36 (ap)	0.726	15.8	71-2	FhG-ISE (7/01)	ECN ¹⁵
Nanocrystalline dye (submodule)	4.7 ± 0.2	141-4 (ap)	0.795	11-3	59.2	FhG-ISE (2/98)	INAP
Multijunction cells							
GaInP/GaAs	30-3	4-0 (t)	2.488	14.22	85.6	JQA (4/96)	Japan Energy (monolithic) ¹⁶
GaInP/GaAs/Ge	28.7 ± 1.4	29-93 (t)	2.571	12.95	86.2	NREL (9/99)	Spectrolab (monolithic)
GaAs/CIS (thin film)	25.8 ± 1.3	4.00 (t)				NREL (11/89)	Kopin/Boeing (4 terminal)
a-Si/CIGS (thin film)g	14.6 ± 0.7	2-40 (ap)				NREL (6/88)	ARCO (4 terminal) ¹⁷

Table I. Confirmed terrestrial cell and submodule efficiencies measured under the global AM1.5 spectrum (1000 Wm^2) at 25°C

^aCIGS = CuInGaSe₂; a-Si = amorphous silicon/hydrogen alloy.

^bEffic. = efficiency.

c(ap) = aperture area; (t) = total area; (da) = designated illumination area.

 d FF = fill factor.

eFhG-ISE = Fraunhofer-Insitut für Solare Energiesysteme; JQA = Japan Quality Assurance.

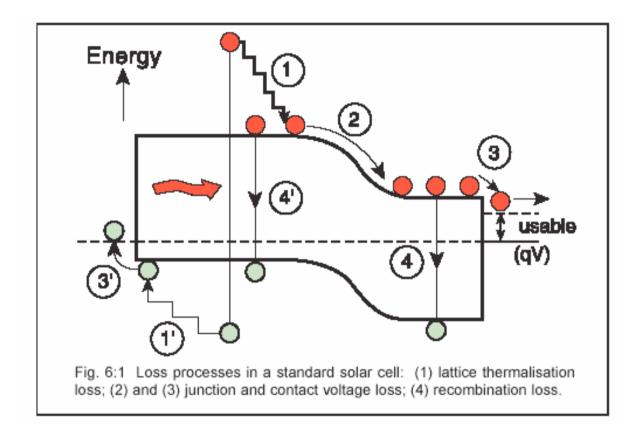
^fNot measured at external laboratory.

^gUnstabilized results.





Efficiency limit for a single junction device



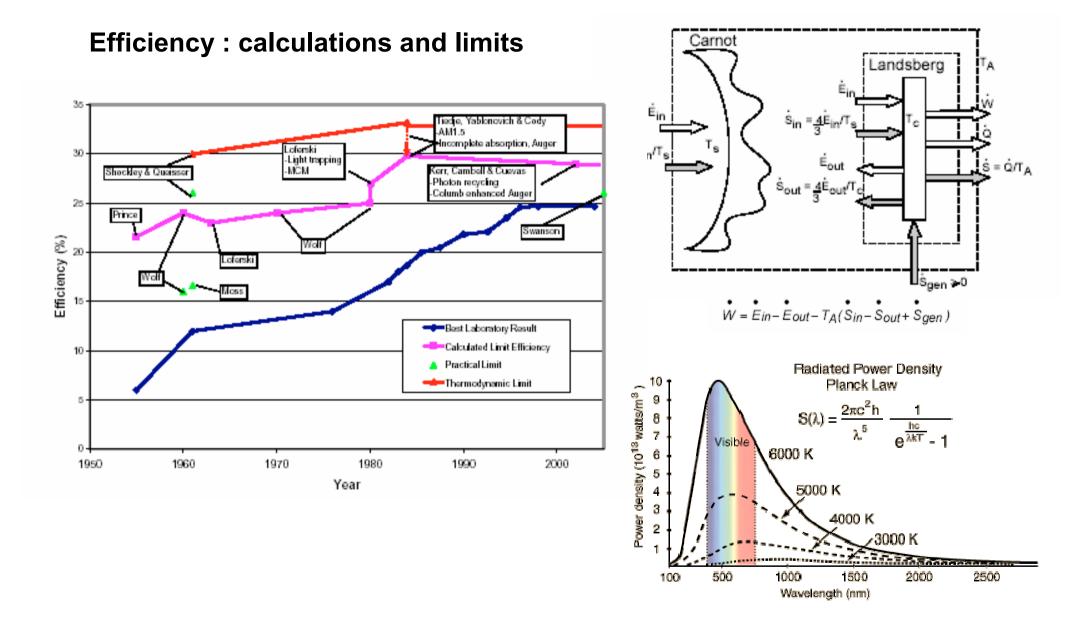
- 1. Photons E>> Eg 20%
- 2. Junction losses 10%
- 3. Non ohmic contacts 10%
- 4. Recombination 30%
- 5. Photons E<Eg 30%

Max 30.8% at 1 sun for silicon

Practical limit about 26%







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Efficiency : calculations and limits

Thermodinamic limit

 η = 1-Ta/Ts = 95% Carnot efficiency $\eta = [1 - (T_c / T_s)^4][1 - T_a / T_s] = 85.4\%$ Müser = 86.8% multiple converters

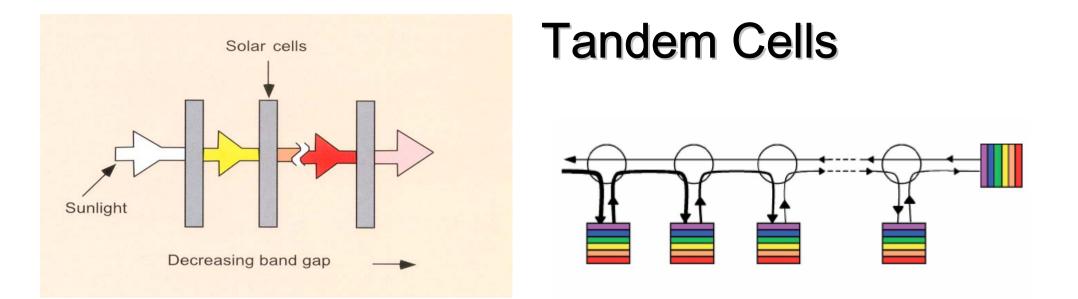
Quantum converter

$$\eta = \frac{x_g \int_{x_g}^{x_\infty} f(x) dx}{\int_{0}^{\infty} x f(x) dx}$$

= 86.8% multiple converters
= 40.8% one converter, max concentration (1/fω = 45.872)
= 30.8% one converter, 1 sun.

$$x = E / KT_s$$
 f(x) = generalized photon distribution function





86,8% theoretical limit for infinite junctions (93.3% con l'uso di circolatori ottici)

30% triple junction (GalnP/GaAs/Ge)

39 % under concentration

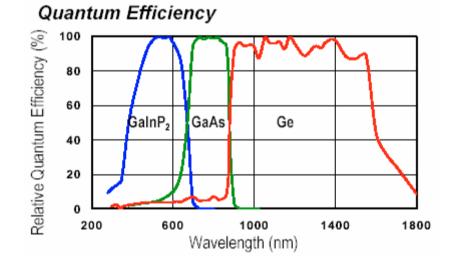
6-12% amorphous silicon best modules

Possible candidate for multigiunctions: InGaN => theoretical limit about 50% Material used for LEDs



Spectrolab Inc. 12500 Gladstone Avenue, Sylmar, California 91342 USA

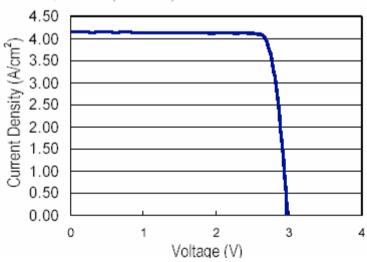
- High efficiency GaInP₂/GaAs/Ge triple junction monolythic, two-terminal design
- Greater than 30% AM1.5D min. avg. efficiency from 200 to 400 Suns concentration in production
- Compatible with point focus, dense array and linear concentrators
- High Reliability
 - -No degradation with multiple assembly methods



Typical Cell Electrical Parameters 350 Suns, AM1.5D (37.2 W/cm²) 25°C

J _{sc} = 4.14 A/cm²	J _{mp} = 4.05 A/cm ²
V _{oc} = 2.97 V	V _{mp} = 2.64 V
P _{mp} = 10.68 W/cm ²	Cff = 86.9 %
Efficiency = 30.5 %	

Typical Cell Light IV Characteristic

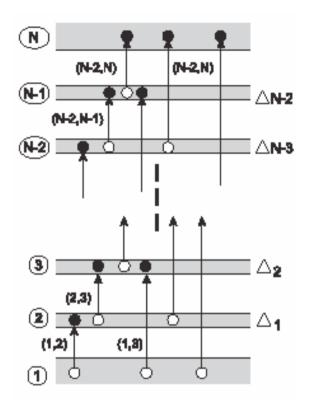


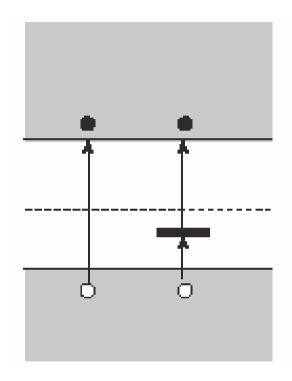
350 Suns, AM1.5D (35 W/cm2) 25°C

EniTecnologie



Multiband and impurity cells

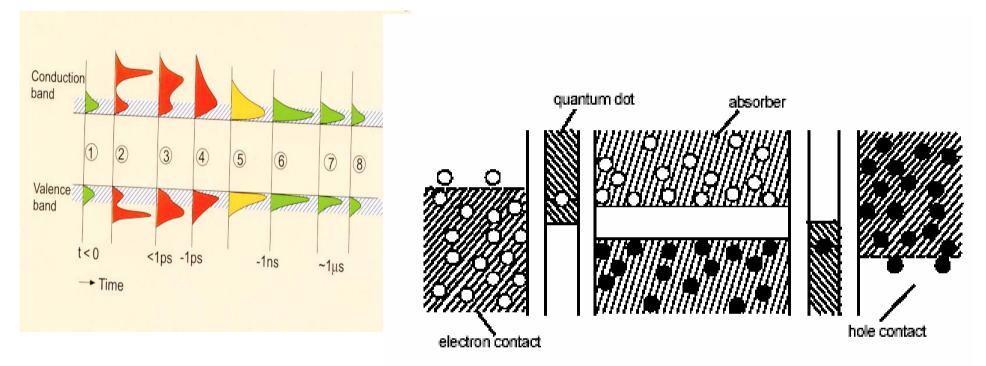




86,8% limit for infinite bands With Quantum Wells or Quantum dots



Hot Carriers



Problems to solve

- Slow cooling system
- Selective contacts





Conclusions

PV is a fast growing sector.

Silicon represents 90% of the market and has potential for further cost reductions, despite the current shortage situation

However, the theoretical efficiency limit is unlikely to be reached in eth near future. Other cell production technologies may be suitable for industrial applications, with efficiency values around 20%

Long term technologies include organic and polimeric cells, and terrestrial use of III-V compounds, which have demonstrated >39% under concentarted light. Higher efficeny structures are under study. Promising candidates are InGaN, used for LEDs, and QD structures such as hot carriers or multiband approaches.



FAQs

• What is the energy pay-back time of a commercial PV module?

In terms of energy, the largest component for the cell is in the realization of silicon. A rough calculation predicts about 1 year for energy recovery of the silicon. Other important components for the modules are teh frames and the glass sheets. This brings the total energy pay back time to 2-3 years for an efficient c-Si module

• How much does a home system cost, and how much space does it occupy?

25 sqm for a 3 kW system. About 22 k€. Annual production (in Rome): 3800 kWh. With the current Italian feed in tariff, return of the investment is in about 10 years.





Thank you!



